



DESCRIPTION

The UM9301 PIN Diode utilizes special overall chip geometry with an extremely thick intrinsic "I" region, to offer unique capabilities in both RF switch and attenuator applications. Volume production also makes the diode an economical choice suitable for many commercial low power equipments. The UM9301 has been designed for use in bridged TEE attenuator circuits commonly utilized for gain and slope control in CATV amplifiers.

Low distortion and high dynamic range are characteristic of the diodes' outstanding performance. The UM9301 is also appropriate for switch applications, when little or no bias voltage is available. Frequent applications occur in portable 12 volt-powered communications equipments, operating at frequencies as low as 2 MHz.

KEY FEATURES

- Specified low distortion
Low distortion properties at low reverse bias
Resistance specified at 3 current points
High reliability fused-in-glass construction

APPLICATIONS/BENEFITS

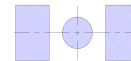
- Little or no Bias required.
Operates as low as 2MHz.
Available in leaded or surface mount packages.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

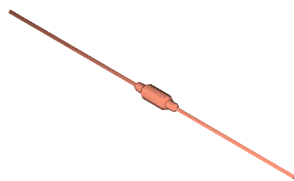
ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

Table with 4 columns: Rating, Symbol, Value, Unit. Rows include Reverse Voltage (75 Volts), Reverse Current (10 uA), Average Power Dissipation (1.0 Watts), Storage Temperature (-65 to 175 °C), and Operating Temperature (-65 to 175 °C).

UM9301SM



UM9301



UM9301SM

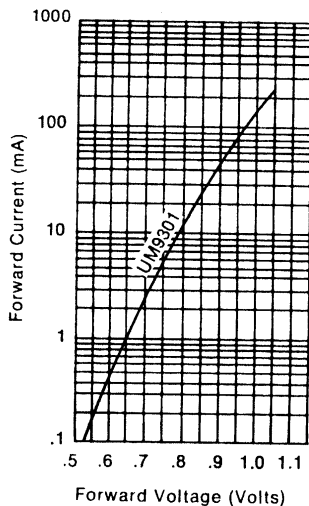
- (1) Mounted on 2" square by 0.06" thick FR4 board with a 1" x 1" square 2-ounce copper pattern..
(2) Lead 1/2 inch. (12.7mm) Total to 25°C Contact.



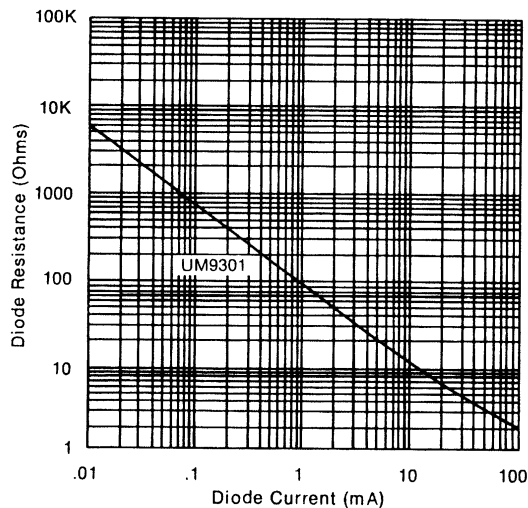
ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ.	Max	Units
► Off Characteristics						
Diode Resistance	R _S	I = 100 mA; f = 100 MHz I = 1 mA; f = 100 MHz I = 0.01 mA; f = 100 MHz	3000	1.7 80 5000	3.0 150	Ω
Current for R _S = 75 Ω I _R	R _S	f = 100 MHz	0.5	1.1	2.0	mA
Return Loss	I	Frequency Range: 10-300MHz R _S = 75 Ω @ 100MHz Diode Terminates 75 Ω line	25			dB
Second Order Distortion	V	f ₁ = 10 MHz; f ₂ = 13 MHz P = 50 dBmV; See Test Circuit		55	50	-dB
		F ₁ = 67 MHz; f ₂ = 77 MHz P = 50 dBmV; See Test Circuit		70		-dB
Third Order Distortion	V	F ₁ = 10 MHz; F ₂ = 13 MHz P = 50 dBmV; See Test Circuit		75	65	-dB
		Triple Beat; 205 +67 -77MHz P = 50 dBmV; See Test Circuit		95		-dB
Cross Modulation Distortion	V	12 Channel Test P = 50 dBmV; See Test Circuit Dix Hills Test Set		75		-dB
Reverse Current	I _R	V = 75 V			10	μA
Carrier Lifetime	τ	I = 10 mA	4.0			μs
► Dynamic characteristics						
Capacitance	C _T	V = 0V; f = 100 MHz			0.8	pF

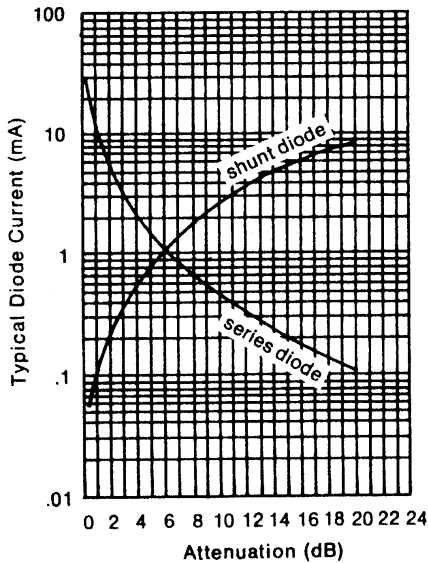
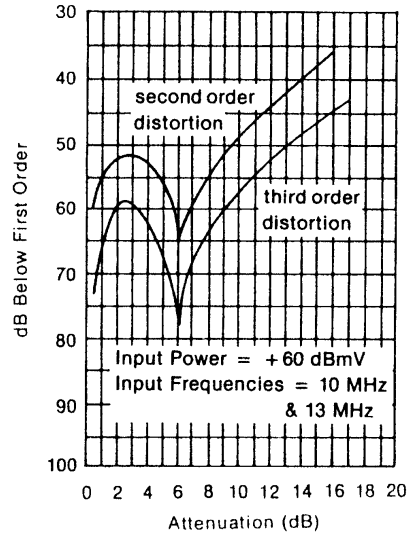
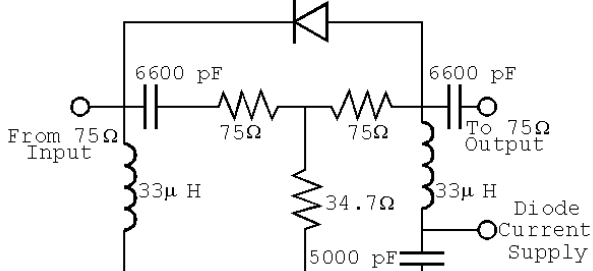
FORWARD CURRENT VS FORWARD VOLTAGE (TYPICAL)



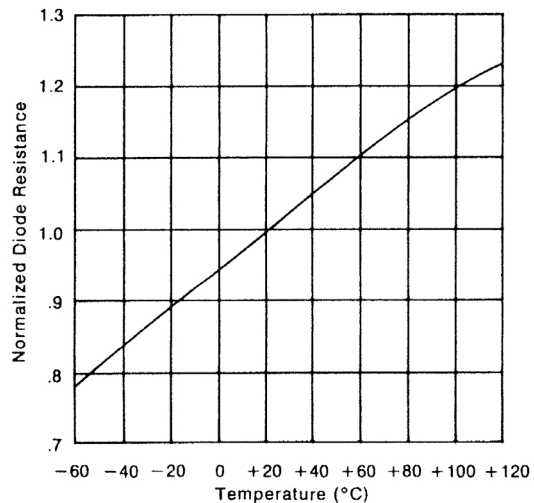
DIODE RESISTANCE VS DIODE CURRENT (TYPICAL)

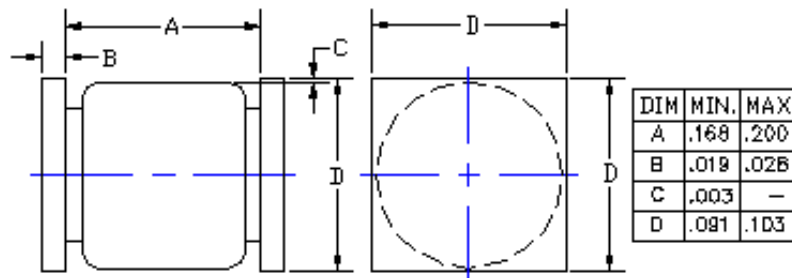


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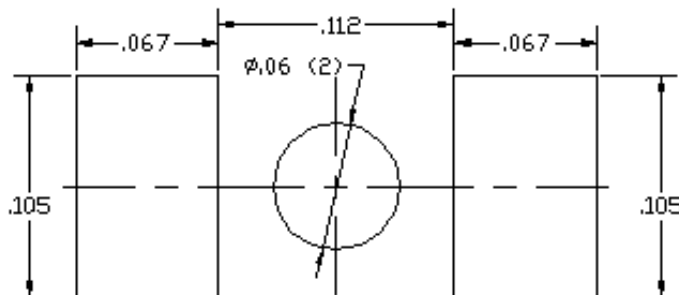
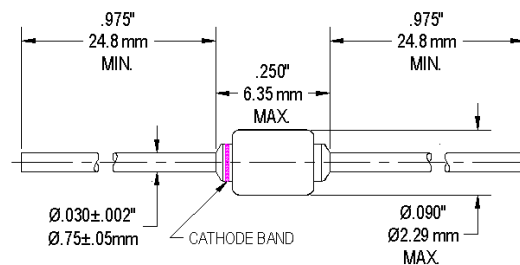
TYPICAL BRIDGED TEE ATTENUATOR PERFORMANCE
DIODE CURRENT VS ATTENUATION UM9301

DISTORTION ATTENUATION

TEST CIRCUIT FOR DISTORTION MEASUREMENTS D.U.T.


Note: Diode Current adjusted for 10dB Attenuation

NORMALIZED R_S VS TEMPERATURE


UM9301SM

NOTES:

1. These dimensions will match the terminals and provide for additional solder fillets at the outboard ends at least as wide as the terminals themselves, assuming accuracy of device placement within .005 inches.
2. If the mounting method chosen requires use of an adhesive separate from the solder compound, a round (or square) spot of cement as shown should be satorially located.
3. Dimensions shown are in inches.

STANDARD SMALL SQUARE END CAP OUTLINE

UM9301

NOTES:

1. BAND INDICATE CATHODE END.



UM9301/UM9301SM

Commercial Attenuator Diode

PRODUCT PREVIEW